



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>

## NTE5426 Silicon Controlled Rectifier (SCR) Sensitive Gate, TO220 Isolated

**Description:**

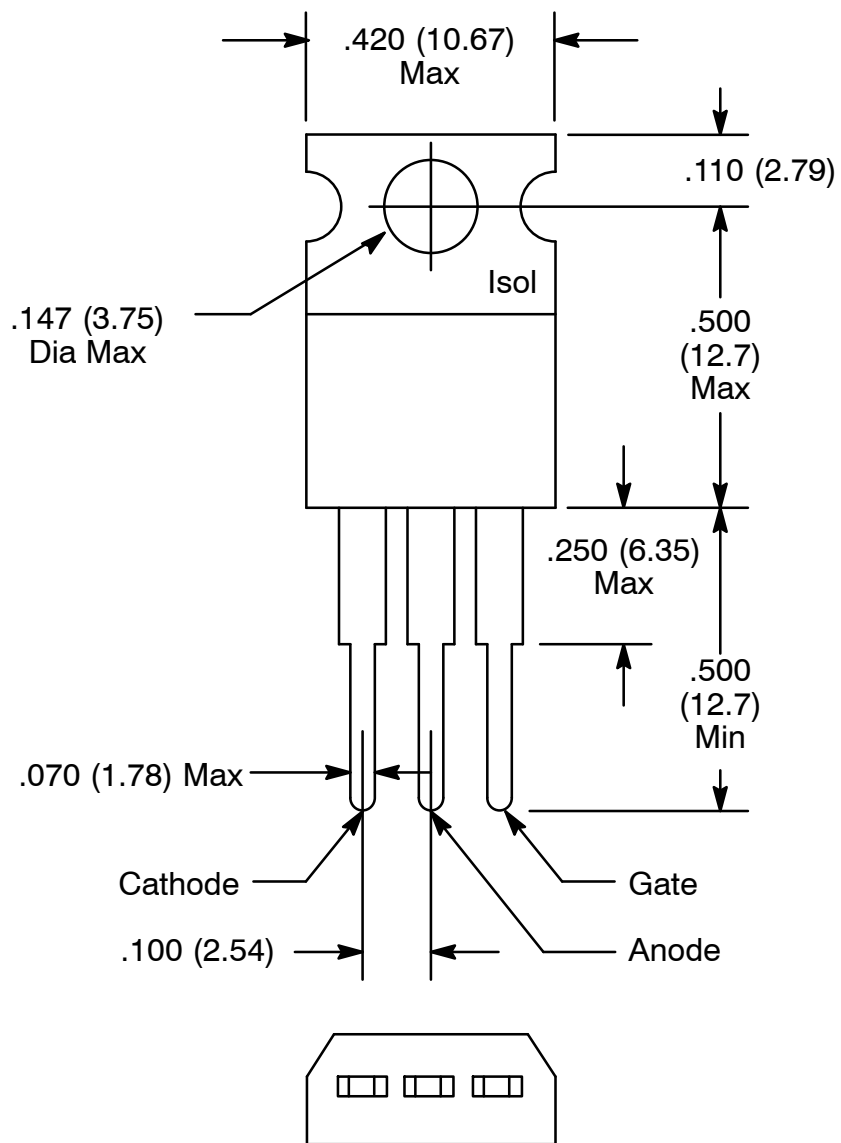
The NTE5426 is silicon controlled rectifier (SCR) in an isolated tab TO220 type package. This device may be switched from off-state to conduction by a current pulse applied to the gate terminal and is designed for control applications in lighting, heating, cooling, and static switching relays.

**Absolute Maximum Ratings:**

Repetitive Peak Off-State Voltage (Gate Open,  $T_C = +110^{\circ}\text{C}$ ),  $V_{DRM}$  ..... 400V  
 Repetitive Peak Reverse Voltage (Gate Open,  $T_C = +110^{\circ}\text{C}$ ),  $V_{RRM}$  ..... 400V  
 RMS On-State Current ( $T_C = +80^{\circ}\text{C}$ ,  $180^{\circ}$  Conduction Angle),  $I_{T(RMS)}$  ..... 10A  
 Peak Surge (Non-Repetitive) On-State Current (One Cycle, 50 or 60Hz),  $I_{TSM}$  ..... 80A  
 Peak Gate-Trigger Current ( $3\mu\text{s}$  max),  $I_{GTM}$  ..... 1A  
 Peak Gate-Power Dissipation ( $I_{GT} = I_{GTM}$ ),  $P_{GM}$  ..... 16W  
 Average Gate Power Dissipation,  $P_{G(AV)}$  ..... 500mW  
 Operating Temperature Range,  $T_{opr}$  .....  $-40^{\circ}$  to  $+100^{\circ}\text{C}$   
 Storage Temperature Range,  $T_{stg}$  .....  $-40^{\circ}$  to  $+150^{\circ}\text{C}$   
 Typical Thermal Resistance, Junction-to-Case,  $R_{thJC}$  .....  $3.0^{\circ}\text{C/W}$

**Electrical Characteristics:** ( $T_C = +25^{\circ}\text{C}$  and "Maximum Ratings" unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Peak Off-State Current	$I_{DRM}$ , $I_{RRM}$	Rated $V_{DRM}$ or $V_{RRM}$ , $T_C = +110^{\circ}\text{C}$ , $R_G - K = 1\text{k}\Omega$	-	-	0.1	mA
Maximum On-State Voltage	$V_{TM}$	$I_T = \text{Rated Amps}$	-	-	2.0	V
Gate Trigger Current, Continuous DC	$I_{GT}$	Anode Voltage = 12V, $R_L = 60\Omega$	-	-	200	$\mu\text{A}$
Gate Trigger Voltage, Continuous DC	$V_{GT}$	Anode Voltage = 12V, $R_L = 60\Omega$	-	-	0.8	V
DC Holding Current	$I_H$	Gate Open, $R_G - K = 1\text{k}\Omega$	-	-	3.0	mA
Turn-On Time	$t_{gt}$	$(t_d + t_r)$ $I_{GT} = 150\text{mA}$	-	-	2.5	$\mu\text{s}$
Critical Rate of Rise of Off-State Voltage	critical $dv/dt$	Gate Open, $T_C = +110^{\circ}\text{C}$ , $R_G - K = 1\text{k}\Omega$	-	8	-	$\text{V}/\mu\text{s}$



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